

High Noise Immunity 42 V Input Voltage 70 mA Voltage Tracker

OVERVIEW

The R1540x is a voltage tracker featuring input voltage in the range of 3.5 V to 42 V. Highly accurate output voltage which attributes to CE/ADJ pin achieves successful sequence control of the integrated off-board sensor module. Strong enough not to require the circuit to avoid external electromagnetic interference (EMI) and this contributes space saving.

KEY BENEFITS

- Excellent noise immunity provides effective shielding against EMI.
- Lower stand-by current consumption leads to energy saving of the whole system to prolong battery life.
- Response to requirements for sequence control in the system with integrated sensors.

KEY SPECIFICATIONS

- Input Voltage Range (Maximum Rating): 3.5 V to 42.0 V (50.0 V)
- Supply Current: Typ. 60 µA
- Standby Current: Typ. 0.1 µA
- Tracking Voltage Range: 2.2 V to 14 V
- Tracking Voltage Accuracy: ± 15 mV
- (−40°C ≤ Ta ≤ 105°C, V_{CE/ADJ} = 5 V)
- Output Current 70 mA
- Ripple Rejection: Typ. 80 dB (f = 100 Hz)
- Protections: Thermal Shutdown, Output Current Limiting and Short-circuit Current Limiting

PACKAGE

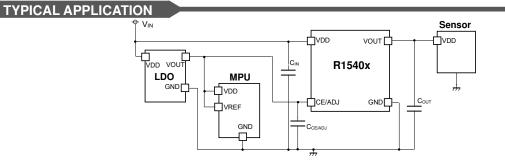




NO.EA-513-200728

SOT-23-5 2.9 x 2.8 x 1.1 (mm)

HSOP-8E 5.2 x 6.2 x 1.45 (mm)



CIN: 0.1uF, COUT: 10µF, CCE/ADJ: 0.1uF, Ceramic capacitor

SELECTION GUIDE

Product Name	Package	Quantity per Reel
R1540N001B-TR-FE	SOT-23-5	3,000 pcs
R1540S001B-E2-FE	HSOP-8E	1,000 pcs

APPLICATIONS

Off-board sensors and power supply systems for analog to digital converters (ADC)

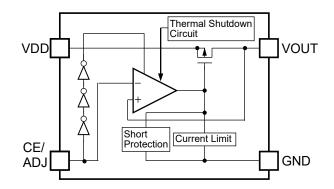
SELECTION GUIDE

R1540x offers selectable packages corresponding to user's purpose.

Selection Guide

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R1540N001B-TR-FE	SOT-23-5	3,000 pcs	Yes	Yes
R1540S001B-E2-FE	HSOP-8E	1,000 pcs	Yes	Yes

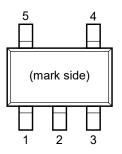
BLOCK DIAGRAM

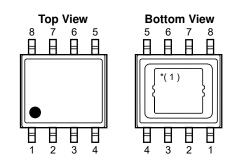


R1540x001B Block Diagram

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PIN DESCRIPTIONS





R1540N (SOT-23-5) Pin Configuration R1540S (HSOP-8E) Pin Configuration

R1540N Pin Descriptions

Pin No.	Symbol	Description
1	CE/ADJ	Chip Enable and Adjustment Pin (Active - High)
2	GND ⁽²⁾	Ground Pin
3	VDD	Input Pin
4	VOUT	Output Pin
5	GND ⁽²⁾	Ground Pin

R1540S Pin Descriptions

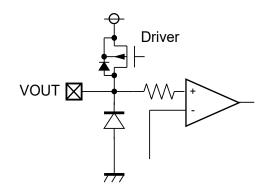
Pin No.	Symbol	Description
1	VDD	Input Pin
2	VDD	Input Pin
3	NC	No Contact
4	CE/ADJ	Chip Enable and Adjustment Pin (Active - High)
5	GND ⁽²⁾	Ground Pin
6	GND ⁽²⁾	Ground Pin
7	NC	No Contact
8	VOUT	Output Pin

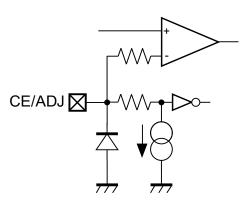
⁽¹⁾ The tab on the bottom of the package is substrate potential (GND). It is recommended that this tab to be connected to the ground plane on the board.

⁽²⁾ The GND pins must be wired together on the board.

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INTERNAL EQUIVALENT CIRCUIT FOR EACH PIN





VOUT Pin Internal Equivalent Circuit Diagrams

CE/ADJ Pin Internal Equivalent Circuit Diagrams

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Rating	Unit
Maria	Input Voltage		-0.3 to 50	V
VIN	Peak Voltage ⁽¹⁾		60	V
V _{CE/ADJ}	CE/ADJ Pin Input Voltage		-0.3 to 50	V
Vout	VOUT Pin Output Voltage		-0.3 to V _{IN} + 0.3 ≤ 50	V
Гоит	Output Current		95	mA
Р	Power Dissipation (2)	SOT-23-5	660	mW
PD	JEDEC STD. 51 HSOP-8E		2900	IIIVV
Tj	Junction Temperature Range		-40 to 125	°C
Tstg	Storage Temperature Range		-55 to 125	°C

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Rating	Unit
VIN	Input Voltage	3.5 to 42	V
V _{CE/ADJ}	CE/ADJ Input Pin Voltage	0 to 14	V
Та	Operating Temperature Range	-40 to 105	°C

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such ratings by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

⁽¹⁾ Duration time: 200 ms.

⁽²⁾ Refer to POWER DISSIPIATION for detailed information

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ELECTRICAL CHARACTERISTICS

 $C_{IN} = 0.1 \ \mu\text{F}$, $C_{OUT} = 10 \ \mu\text{F}$, $V_{CE/ADJ} = 5.0 \ V$ and $V_{IN} = 14.0 \ V$, unless otherwise noted.

The specifications surrounded by are guaranteed by design engineering at $-40^{\circ}C \le Ta \le 105^{\circ}C$.

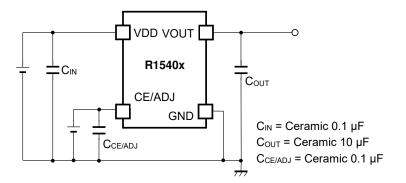
R1540x001B Electrical Characteristics

(Ta = 25°C) Symbol Parameter Conditions Min. Max. Unit Typ. Supply Current $V_{IN} = 14 V, I_{OUT} = 0 mA$ 60 100 μA lss $V_{IN} = 42 V, V_{CE/ADJ} = 0 V$ Istandby Standby Current 0.1 1.0 μA $8 \text{ V} \leq \text{V}_{\text{IN}} \leq 24 \text{ V}$ 1 mA ≤ lout ≤ 70 mA -15 15 $V_{CE/ADJ} = 5.0 V$ mV $6 V \leq V_{IN} \leq 42 V$ Tracking Voltage Accuracy ΔVo $1 \text{ mA} \leq I_{OUT} \leq$ 10 mA $2.2 \text{ V} \leq \text{V}_{\text{CE/ADJ}} \leq 5.0 \text{ V}$ -15 15 V_{IN} = 15 V mV 18 $I_{OUT} = 1 \text{ mA}$ $5.0 \text{ V} < \text{V}_{\text{CE/ADJ}} \le 14.0 \text{ V}$ -18 ΔV out V_{IN} = 8 V, 1 mA ≤ I_{OUT} ≤ 70 mA -2 Load Regulation 2 mV $/\Delta I_{OUT}$ ΔV out -8 Line Regulation $6 \text{ V} \leq \text{V}_{\text{IN}} \leq 42 \text{ V}, \text{ I}_{\text{OUT}} = 1 \text{ mA}$ 8 mV $/\Delta V_{IN}$ $2.2 \text{ V} \leq \text{V}_{\text{CE/ADJ}} \leq 14 \text{ V}, \text{I}_{\text{OUT}} = 1 \text{ mA},$ ΔV_{OUT} -1 1 mV/V **CE/ADJ Regulation** $V_{IN} = 15 V$ $/\Delta V_{CE/ADJ}$ 2.1 IOUT = 70 mA 1.3 V VDIF **Dropout Voltage** $V_{IN} = 8 V$ 80 120 LIM **Output Current Limit** mΑ 20 $V_{IN} = 8 V$, $V_{OUT} = 0 V$ Isc Short Current Limit 40 mΑ CE/ADJ Pin Input Voltage, V_{CE/ADJH} $V_{IN} = 15 V$ 2.0 14 V high CE/ADJ Pin Input Voltage, 0 1.0 V $V_{IN} = 42 V$ VCE/ADJL low CE/ADJ Pin Pull Down 1.0 $V_{IN} = 42 V, V_{CE/ADJ} = 2 V$ 0.2 **I**PD μA Current Thermal Shutdown Detection °C TTSD Junction Temperature 150 165 Temperature Thermal Shutdown Released **T**_{TSR} Junction Temperature 128 135 °C Temperature All test items listed under Electrical Characteristics are done under the pulse load condition (Tj \approx Ta = 25°C).

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TYPICAL APPLICATION

TYPICAL APPLICATION





TECHNICAL NOTES

Phase Compensation

R1540x adopts capacitance and Equivalent Series Resistance (ESR) for phase compensation to ensure stable operation even with load varying current. For this end, the capacitor of 10 μ F or more is essential. A certain amount of ESR may cause unstable output voltage. Fully take temperature and frequency characteristics into consideration when evaluating the circuit. Place the capacitor of 0.1 μ F or more between VDD and GND with using short leads and short printed circuit traces.

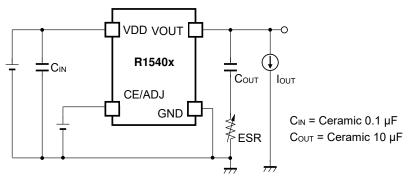
PCB Layout

SOT-23-5 package: connect Nos. 2 and 5 of GND pin together. HSOP-8E package: connect Nos. 5 and 6 of GND pin together.

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ESR vs. output current characteristics

Using ceramic output capacitor is highly recommended although availability of another low-ESR capacitors. The mutual relations between the output current (I_{OUT}) causes noise under the specified value and the ESR are indicated below for reference.



Measurement Conditions

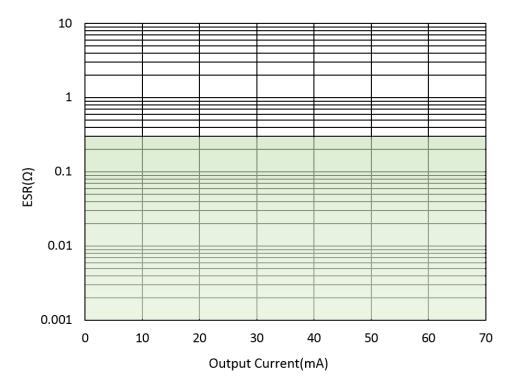
Frequency Band: 10 Hz to 2 MHz

Temperature: -40°C to 105°C

Shaded portion: Noise level is 40 µV (average) or below

Capacitors: C_{IN} = 0.1 μF of Ceramic, C_{OUT} = 10 μF of Ceramic

R1540x001B



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THEORY OF OPERATION

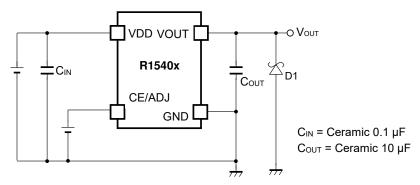
Thermal Shutdown

Thermal Shutdown occurs when the device's junction temperature reaches 165°C (Typ.) at which point the regulator will automatically shut down. Then the regulator resumes from the stand-by state when the junction temperature decreases below 135°C (Typ.). Unless the cause of overheating is eliminated, the device cycles on and off to generate pulse output.

APPLICATION INFORMATION

Typical Application for IC Chip Breakdown Prevention

A sudden surge of current flowing through the VOUT pin during a short to GND leads to negative voltage due to resonance generated between the impedance of the wire and the output capacitor, C2. Consequently, large short-circuit current may destroy the IC or a load device in some types of pattern boards. It is highly recommended to connect schottky diode, D1, between VOUT pin and GND to prevent the IC from being destroyed.



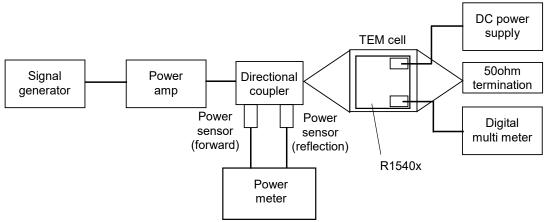
R1540x Typical Application for IC Chip Breakdown Prevention

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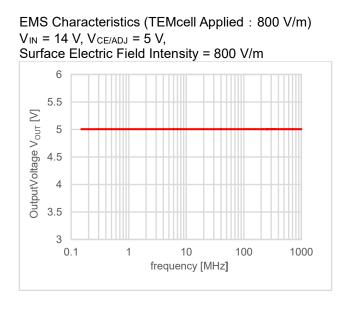
Electromagnetic Noise Immunity

An output voltage may linearly varies in some regulators due to electromagnetic noise. R1540x adopts the techniques on its circuits to prevent this voltage variation. The noise immunity test indicated below was conducted to confirm that R1540x is fairly robust to electromagnetic noise over a broad frequency band.

DC power supply : apply $V_{IN} = 14 V$, $V_{CE/ADJ} = 5 V$ Digital multi meter : measure the output DC voltage of R1540 Signal generator : apply high frequency signal of 150 kHz to1 GHz Power meter : measure the intensity of signal so as to sense the surface electric field intensity of 800 V/m



Block Diagram for Immunity Test Based on IEC 62132-2 TEM cell



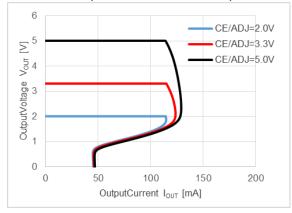
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TYPICAL CHARACTERISTICS

Typical Characteristics are intended to be used as reference data, they are not guaranteed

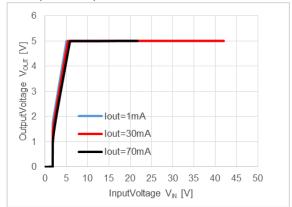
1) Output voltage vs Output Current

 C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF, Ta = 25°C

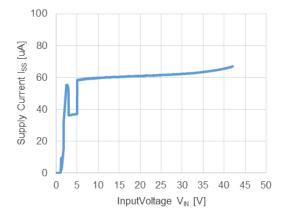


2) Output voltage vs Input Voltage

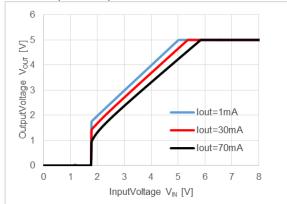
 C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF , Ta=25°C V_{IN} = 0 V,<=>42 V, $V_{CE/ADJ}$ = 5 V



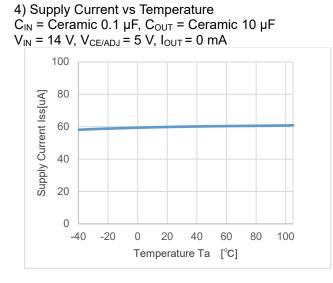
3) Supply Current vs Input Voltage C_{IN} = Ceramic 0.1 μ F, C_{OUT} = Ceramic 10 μ F, Ta = 25°C V_{IN} = 0 V <=>42 V, V_{CE/ADJ} = 5 V, I_{OUT} = 0 mA



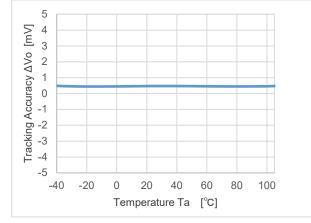
V_{IN} = 0 V,<=> 8 V, V_{CE/ADJ} = 5 V



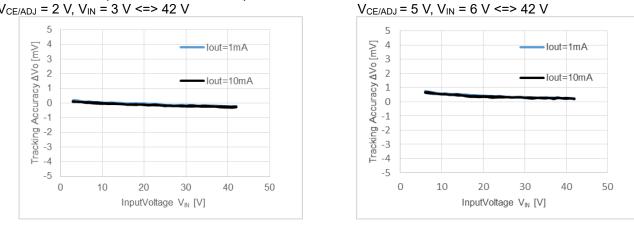
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5) Tracking Accuracy vs Temperature C_{IN} = Ceramic 0.1 μ F, C_{OUT} = Ceramic 10 μ F V_{IN} = 14 V, V_{CE/ADJ} = 5 V, I_{OUT} = 1 mA

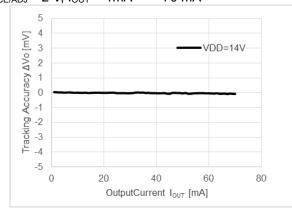


6) Tracking Accuracy vs Input Voltage C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF, Ta=25°C $V_{CE/ADJ}$ = 2 V, V_{IN} = 3 V <=> 42 V

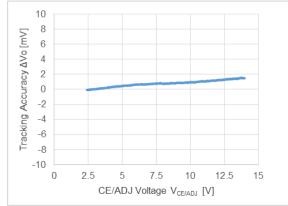


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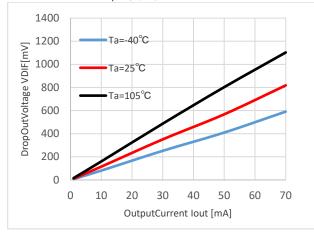
7) Tracking Accuracy vs Load Current C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF, Ta = 25°C $V_{CE/ADJ}$ = 2 V, I_{OUT} = 1mA <=> 70 mA

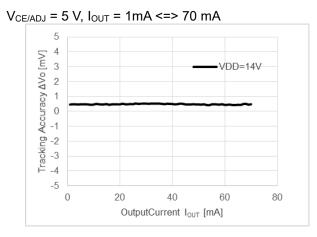


8) Tracking Accuracy vs CE/ADJ Voltage C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF, Ta = 25°C V_{IN} = 15 V, $V_{CE/ADJ}$ = 2.4 V <=> 14 V, I_{OUT} = 1 mA



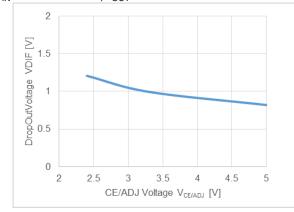
9) Dropout Voltage vs Output Current C_{IN} = Ceramic 0.1 μ F, C_{OUT} = Ceramic 10 μ F, Ta=25°C V_{IN} = 0 V <=> 22 V, V_{CE/ADJ} = 5 V



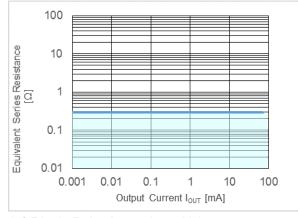


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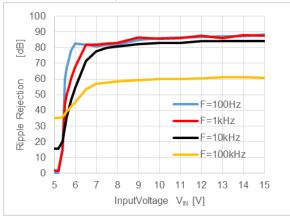
10) Dropout Voltage vs CE/ADJ Voltage C_{IN} = Ceramic 0.1 μ F, C_{OUT} = Ceramic 10 μ F, Ta=25°C V_{IN} = 0 V <=>22 V, I_{OUT}=70 mA



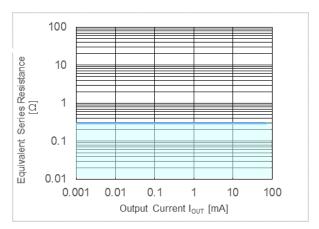
11) Equivalent Series Resistance vs Output Current C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10µF, Ta=25°C V_{IN} = 4 V <=> 42 V, V_{CE/ADJ} = 2 V Ta =-40°C / 25°C / 105°C



12) Ripple Rejection vs Input Voltage C_{IN} = none, C_{OUT} = Ceramic 10 µF, Ta = 25°C V_{IN} = 5 V <=> 15 V, $V_{CE/ADJ}$ = 5 V

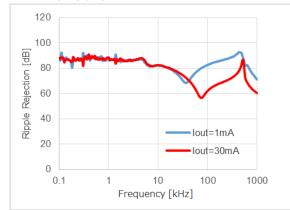


V_{IN} = 7 V <=> 42 V, V_{CE/ADJ} = 5 V Ta=-40°C / 25°C / 105°C



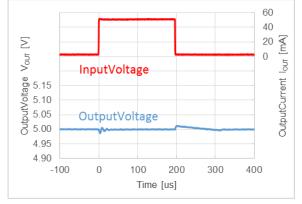
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13) Ripple Rejection vs Frequency C_{IN} = none, C_{OUT} = Ceramic 10 μ F, Ta = 25°C V_{IN} = 14 V, V_{CE/ADJ} = 2 V

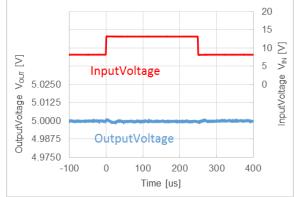


14) Load Transient Response

 C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF, Ta = 25°C V_{IN}=14 V, I_{OUT} = 1 mA <=> 50 mA, tR = tF = 1us

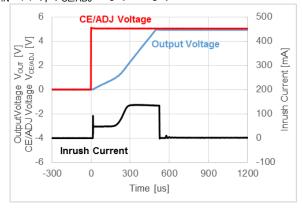


15) Input Transient Response C_{IN} = none, C_{OUT} = Ceramic 10 µF, Ta = 25°C

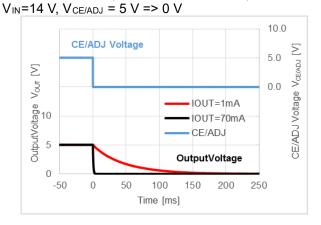


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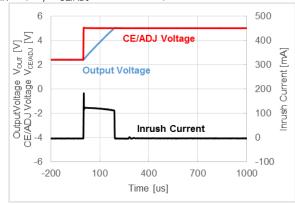
16) Turn-on Speed with CE/ADJ pin C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF, Ta = 25°C V_{IN} =14 V, $V_{CE/ADJ}$ = 0 V => 5 V



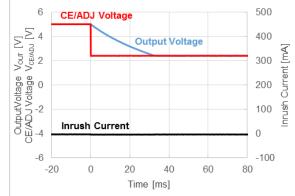
17) Turn-off Speed with CE/ADJ pin C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10µF, Ta = 25°C



18) CE/ADJ Excess/Inrush Current C_{IN} = none, C_{OUT} = Ceramic 10 μ F, Ta = 25°C V_{IN} = 8 V, V_{CE/ADJ} = 2.4 V => 5 V



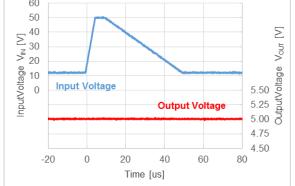




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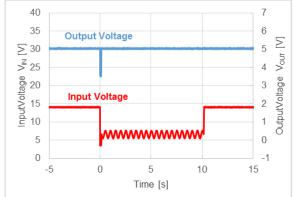
19) Load Dump



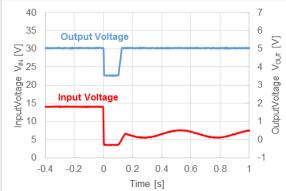


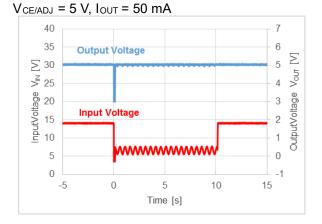
20) Cranking

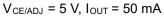
 C_{IN} = Ceramic 0.1 µF, C_{OUT} = Ceramic 10 µF, Ta = 25°C $V_{CE/ADJ}$ = 5 V, I_{OUT} = 1 mA

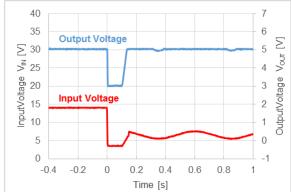






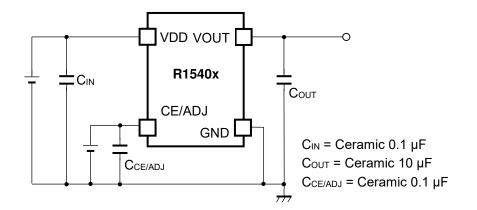






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Test Circuit



R1540x circuit for measuring Typical Characteristics

Measurement Components of Typical Characteristics

Symbol	Capacitance	Measurement item	Manufacturer	Parts number
CIN	0.1 µF	All	TDK	CGA4J2X7R2A104K125AA
Соит	10 µF	All	TDK	CGA6P1X7R1E106K

POWER DISSIPATION

SOT-23-5

Ver. A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

Measurement Conditions

Item	Measurement Conditions	
Environment	Mounting on Board (Wind Velocity = 0 m/s)	
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)	
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm	
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square	
Through-holes	φ 0.3 mm × 7 pcs	

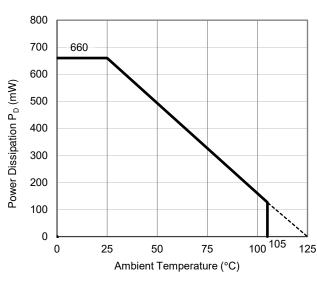
Measurement Result

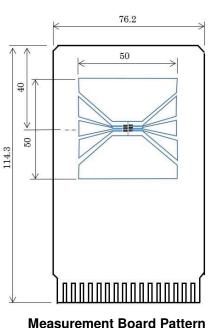
(Ta = 25°C, Tjmax = 125°C)

Item	Measurement Result
Power Dissipation	660 mW
Thermal Resistance (θ ja)	θja = 150°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 51°C/W

θja: Junction-to-Ambient Thermal Resistance

wjt: Junction-to-Top Thermal Characterization Parameter





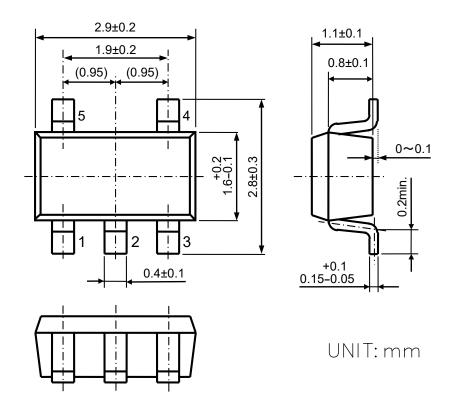
Power Dissipation vs. Ambient Temperature

Measurement Board Pattern

SOT-23-5

Ver. A

i





POWER DISSIPATION

HSOP-8E

Ver. A

The power dissipation of the package is dependent on PCB material, layout, and environmental conditions. The following measurement conditions are based on JEDEC STD. 51-7.

Measurement Conditions

Item	Measurement Conditions	
Environment	Mounting on Board (Wind Velocity = 0 m/s)	
Board Material	Glass Cloth Epoxy Plastic (Four-Layer Board)	
Board Dimensions	76.2 mm × 114.3 mm × 0.8 mm	
Copper Ratio	Outer Layer (First Layer): Less than 95% of 50 mm Square Inner Layers (Second and Third Layers): Approx. 100% of 50 mm Square Outer Layer (Fourth Layer): Approx. 100% of 50 mm Square	
Through-holes	φ 0.3 mm × 21 pcs	

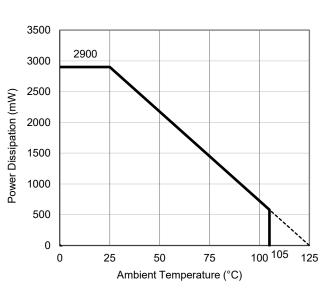
Measurement Result

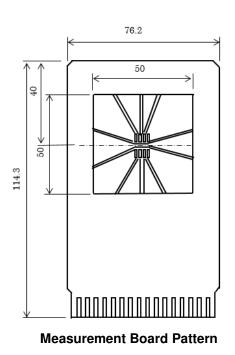
(Ta = 25°C, Tjmax = 125°C)

Item	Measurement Result
Power Dissipation	2900 mW
Thermal Resistance (θja)	θja = 34.5°C/W
Thermal Characterization Parameter (ψjt)	ψjt = 10°C/W

 θ ja: Junction-to-ambient thermal resistance.

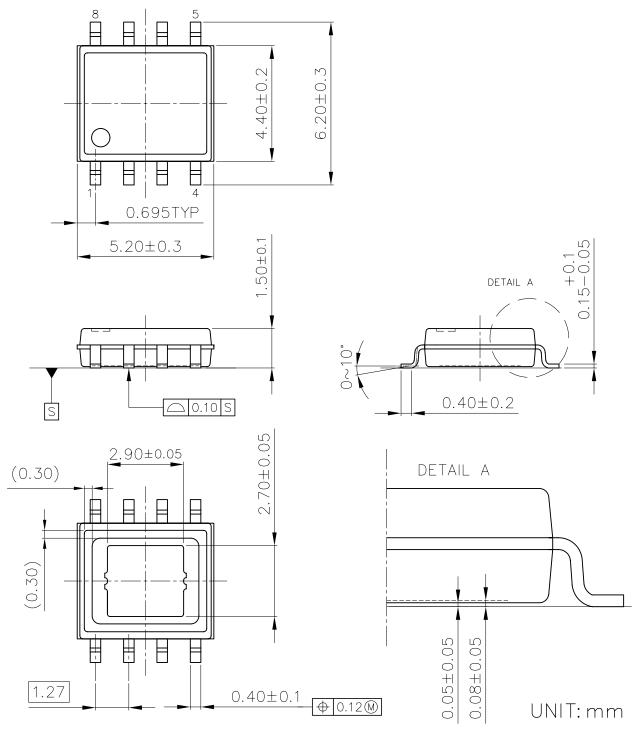
wjt: Junction-to-top of package thermal characterization parameter





Power Dissipation vs. Ambient Temperature

PACKAGE DIMENSIONS



HSOP-8E Package Dimensions

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